

K7Z167288B  
K7Z163688B

*Preliminary*  
**512Kx36 & 256Kx72 DLW(Double Late Write) RAM**

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**Document Title**

512Kx36 & 256Kx72 DLW(Double Late Write) RAM

**Revision History**

<u>Rev. No.</u>	<u>History</u>	<u>Draft Date</u>	<u>Remark</u>
0.0	1. Initial document.	Feb. 10, 2003	Preliminary
0.1	1. Correct the ZQ to programmable.	Mar. 8, 2003	Preliminary

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The attached data sheets are prepared and approved by SAMSUNG Electronics. SAMSUNG Electronics CO., LTD. reserve the right to change the specifications. SAMSUNG Electronics will evaluate and reply to your requests and questions on the parameters of this device. If you have any questions, please contact the SAMSUNG branch office near your office, call or contact Headquarters.

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**K7Z167288B  
K7Z163688B**

**512Kx36 & 256Kx72 DLW(Double Late Write) RAM**

**512Kx36 & 256Kx72-Bit DLW(Dobule Late Write) RAM**

**FEATURES**

- Double Late Write mode , Pipelined Read mode.
- Compatible with Double Late Write Sigma RAM™ x36/x72.
- 1.8V+150/-100 mV Power Supply.
- I/O Supply Voltage 1.5V+0.1V/-0.1V for 1.5V I/O
- HSTL I/O
- Byte Writable Function.
- Single READ/WRITE control pin.
- Self-Timed Write Cycle.
- Complement echo clock outputs
- Programmable impedance output buffer(ZQ)
- 2 User programmable chip enable inputs for easy depth expansion.(EP2, EP3)
- Supports linear burst mode only.
- Slow Down Function.(SD)
- IEEE 1149.1 JTAG Compatible Boundary Scan
- 209 bump, 14mm x 22mm, 1mm bump pitch BGA package
- 209BGA(11x19 Ball Grid Array Package).

**GENERAL DESCRIPTION**

The K7Z163688B & K7Z167288B is 18,874,368-bits Synchronous Static SRAMs.

The Double Late Write RAM utilizes all the bandwidth in any combination of operating cycles.

Address, data inputs, and all control signals except EP2, EP3, and  $\overline{SD}$  are synchronized to input clock.

Write cycles are internally self-timed and initiated by the rising edge of the clock input. This feature eliminates complex off-chip write pulse generation and provides increased timing flexibility for incoming signals.

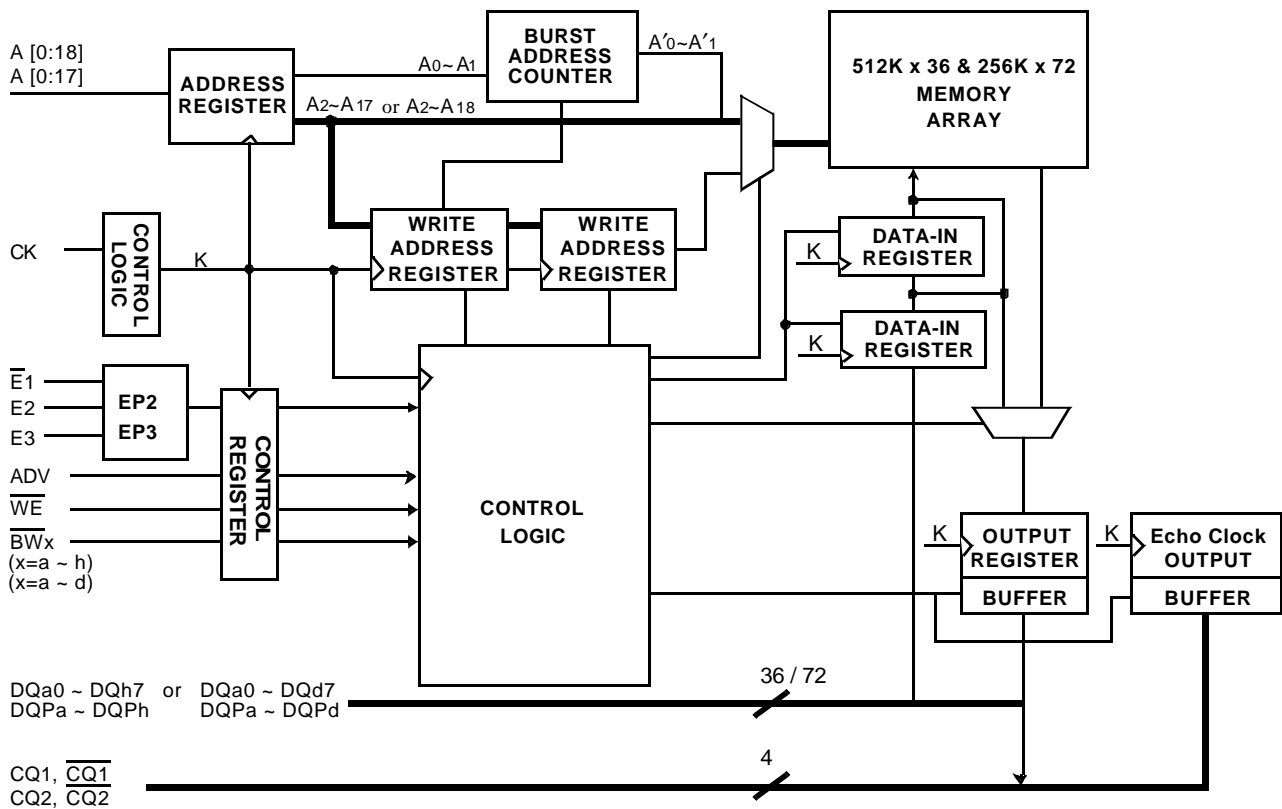
For read cycles,the SRAM output data is temporarily stored by an edge triggered output register and then released to the output buffers at the next rising edge of clock.

The K7Z163688B & K7Z167288B are implemented with SAM-SUNG's high performance CMOS technology and is available in 209BGA packages. Multiple power and ground pins minimize ground bounce.

**FAST ACCESS TIMES**

PARAMETER	Symbol	-35	Unit
Cycle Time	tCYC	2.85	ns
Clock Access Time	tCD	1.7	ns

**LOGIC BLOCK DIAGRAM**



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209BGA PACKAGE PIN CONFIGURATIONS (TOP VIEW)

512Kx36 Common I/O-Top View

	1	2	3	4	5	6	7	8	9	10	11
A	NC	NC	A	E2	A	ADV	A	E3	A	DQb	DQb
B	NC	NC	$\overline{BWc}$	NC	A	$\overline{WE}$	A	$\overline{BWb}$	NC	DQb	DQb
C	NC	NC	NC	$\overline{BWd}$	NC(128M)	$\overline{E1}$	NC	NC	$\overline{BWa}$	DQb	DQb
D	NC	NC	Vss	Vref	NC	MCL	NC	Vref	Vss	DQb	DQb
E	NC	DQPc	VDDQ	VDDQ	VDD	VDD	VDD	VDDQ	VDDQ	NC	DQPb
F	DQc	DQc	Vss	Vss	Vss	ZQ	Vss	Vss	Vss	NC	NC
G	DQc	DQc	VDDQ	VDDQ	VDD	EP2	VDD	VDDQ	VDDQ	NC	NC
H	DQc	DQc	Vss	Vss	Vss	EP3	Vss	Vss	Vss	NC	NC
J	DQc	DQc	VDDQ	VDDQ	VDD	MCH	VDD	VDDQ	VDDQ	NC	NC
K	CQ2	$\overline{CQ2}$	CK	Vref	Vss	MCL	Vss	NC	NC	$\overline{CQ1}$	CQ1
L	NC	NC	VDDQ	VDDQ	VDD	MCH	VDD	VDDQ	VDDQ	DQa	DQa
M	NC	NC	Vss	Vss	Vss	MCL	Vss	Vss	Vss	DQa	DQa
N	NC	NC	VDDQ	VDDQ	VDD	$\overline{SD}$	VDD	VDDQ	VDDQ	DQa	DQa
P	NC	NC	Vss	Vss	Vss	MCL	Vss	Vss	Vss	DQa	DQa
R	DQPd	NC	VDDQ	VDDQ	VDD	VDD	VDD	VDDQ	VDDQ	DQPa	NC
T	DQd	DQd	Vss	Vref	NC	MCL	NC	Vref	Vss	NC	NC
U	DQd	DQd	NC	A	NC(64M)	A	NC(32M)	A	NC	NC	NC
V	DQd	DQd	A	A	A	A1	A	A	A	NC	NC
W	DQd	DQd	TMS	TDI	A	A0	A	TDO	TCK	NC	NC

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512Kx36 &amp; 256Kx72 DLW(Double Late Write) RAM

## 209BGA PACKAGE PIN CONFIGURATIONS (TOP VIEW)

## 256Kx72 Common I/O-Top View

	1	2	3	4	5	6	7	8	9	10	11
A	DQg	DQg	A	E2	A	ADV	A	E3	A	DQb	DQb
B	DQg	DQg	$\overline{BWc}$	$\overline{BWg}$	NC	$\overline{WE}$	A	$\overline{BWb}$	$\overline{BWf}$	DQb	DQb
C	DQg	DQg	$\overline{BWh}$	$\overline{BWd}$	NC(128M)	$\overline{E1}$	NC	$\overline{BWe}$	$\overline{BWa}$	DQb	DQb
D	DQg	DQg	Vss	Vref	NC	MCL	NC	Vref	Vss	DQb	DQb
E	DQPg	DQPc	VDDQ	VDDQ	VDD	VDD	VDD	VDDQ	VDDQ	DQPf	DQPb
F	DQc	DQc	Vss	Vss	Vss	ZQ	Vss	Vss	Vss	DQf	DQf
G	DQc	DQc	VDDQ	VDDQ	VDD	EP2	VDD	VDDQ	VDDQ	DQf	DQf
H	DQc	DQc	Vss	Vss	Vss	EP3	Vss	Vss	Vss	DQf	DQf
J	DQc	DQc	VDDQ	VDDQ	VDD	MCH	VDD	VDDQ	VDDQ	DQf	DQf
K	CQ2	$\overline{CQ2}$	CK	Vref	Vss	MCL	Vss	NC	NC	$\overline{CQ1}$	CQ1
L	DQh	DQh	VDDQ	VDDQ	VDD	MCH	VDD	VDDQ	VDDQ	DQa	DQa
M	DQh	DQh	Vss	Vss	Vss	MCL	Vss	Vss	Vss	DQa	DQa
N	DQh	DQh	VDDQ	VDDQ	VDD	$\overline{SD}$	VDD	VDDQ	VDDQ	DQa	DQa
P	DQh	DQh	Vss	Vss	Vss	MCL	Vss	Vss	Vss	DQa	DQa
R	DQPd	DQPd	VDDQ	VDDQ	VDD	VDD	VDD	VDDQ	VDDQ	DQPa	DQPe
T	DQd	DQd	Vss	Vref	NC	MCL	NC	Vref	Vss	DQe	DQe
U	DQd	DQd	NC	A	NC(64M)	A	NC(32M)	A	NC	DQe	DQe
V	DQd	DQd	A	A	A	A1	A	A	A	DQe	DQe
W	DQd	DQd	TMS	TDI	A	A0	A	TDO	TCK	DQe	DQe

**Pin Description Table**

Pin Name	Description	Type	Comments
A	Address	Input	-
ADV	Advance	Input	Active High
$\overline{BW}_x(x=a-h \text{ or } a-d)$	Byte Write Enable	Input	Active Low
CK	Clock	Input	Active High
DQ	Data I/O	Input/Output	-
CQ	Echo Clock Outputs	Output	Active High
$\overline{CQ}$	Echo Clock Outputs	Output	Active Low
$\overline{E1}$	Chip Enable	Input	Active Low
E2 & E3	Chip Enable	Input	Programmable Active High or Low
EP2 & EP3	Chip Enable Program Pin	Input	-
$\overline{SD}$	Slow Down Input	Input	Active Low
TCK	Test Clock	Input	Active High
TDI	Test Data In	Input	-
TDO	Test Data Out	Output	-
TMS	Test Mode Select	Input	-
MCH	Must Connect High	Input	Active High
MCL	Must Connect Low	Input	Active Low
NC	No Connect	-	Not connected to die
$\overline{WE}$	Write	Input	Active Low
V <sub>DD</sub>	Core Power Supply	Input	1.8V
V <sub>DDQ</sub>	Output Driver Power Supply	Input	1.5V
V <sub>SS</sub>	Ground	Input	-
ZQ	Output Impedance Control	Input	Programmable ZQ
V <sub>ref</sub>	Input Reference Voltage	Input	-

**FUNCTION DESCRIPTION**

The K7Z163688B & K7Z167288B are Double Late Write RAM designed to sustain 100% bus bandwidth by eliminating turnaround cycle when there is transition from Read to Write, or vice versa.

Because a Double Late Write RAM is a synchronous device, address, data Inputs, and read/write control inputs are captured on the rising edge of the input clock. EP2 , EP3 and  $\overline{SD}$  are asynchronous control input.

Read operation is initiated when at the rising edge of the clock, the address presented to the address inputs are latched in the address register, all three chip enables( $\overline{E1}$ , E2, E3) are active, the write enable input signals  $\overline{WE}$  are driven high, and ADV driven low. The internal array is read between the first rising edge and the second rising edge of the clock and the data is latched in the output register. At the second clock edge the data is driven out of the SRAM.

Write operation occurs when  $\overline{WE}$  is driven low at the rising edge of the clock.  $\overline{BWx[h:a]}$  can be used for byte write operation.

The Double Late Write RAM uses a double-late write cycle to utilize 100% of the bandwidth.

At the first rising edge of the clock,  $\overline{WE}$  and address are registered, and the data associated with that address is required two cycle later.

Subsequent addresses are generated by ADV High for the burst access as shown below. The starting point of the burst sequence is provided by the external address. The burst address counter wraps around to its initial state upon completion.

Double Late Write RAM supports linear burst sequence only.

**BURST SEQUENCE TABLE (Linear Burst Order)**

	A[1:0]	A[1:0]	A[1:0]	A[1:0]
1st address	00	01	10	11
2nd address	01	10	11	00
3rd address	10	11	00	01
4th address	11	00	01	10

**Slow Down Function**

$\overline{SD}$  is helpful to prevent to bus contention in read operation after write operation , especially high frequency application.

When  $\overline{SD}$  is Low, the SRAM is operated in a slow down mode. In a slow down mode, the enable/disable timings of output data become slower , which are defined as tKHQV,tKHQZ,tKHQX,tKHQX1/tKHCH and tKLCL.

The valid data window in slow down mode is same with normal operation mode , so it will be helpful in read operation after write operation

When  $\overline{SD}$  is High , the SRAM returns to normal operation node.

The state of  $\overline{SD}$  must be fixed before operation , and it can not be changed during operation.

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**Programmable Enables**

Double Late Write RAM features two user programmable chip enable inputs, E2 and E3. The sense of the inputs, whether they function as active low or active high inputs, is determined by the state of the programming inputs, EP2 and EP3. For example, if EP2 is held at VDD, E2 functions as an active high enable. If EP2 is held to VSS, E2 functions as an active low chip enable input.

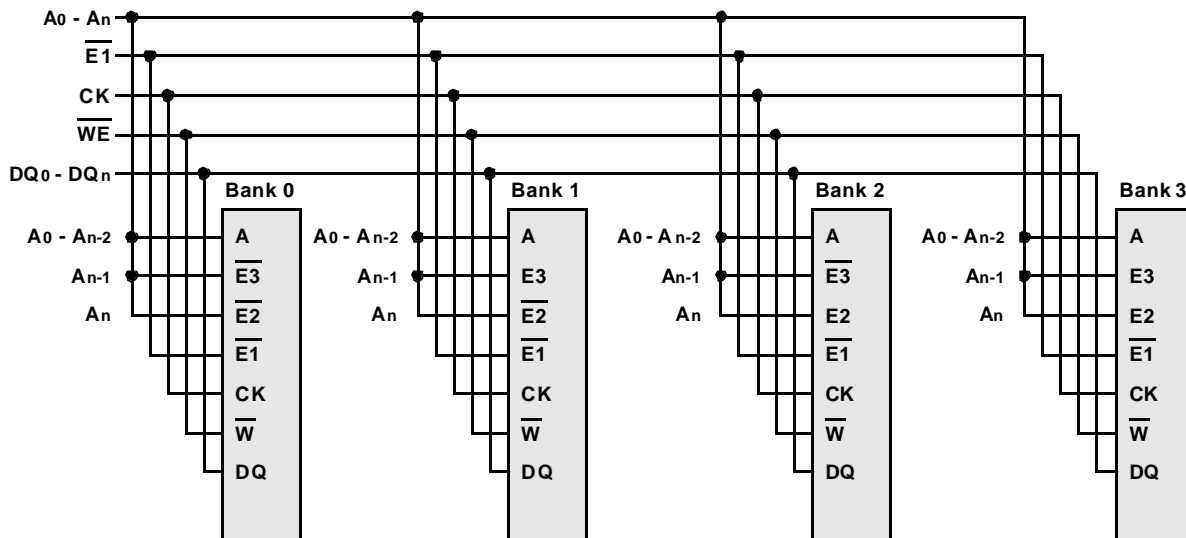
Programmability of E2 and E3 allows four banks of depth expansion to be accomplished with no additional logic. By programming the enable inputs of four Double Late Write RAMs in binary sequence(00, 01, 10, 11)and driving the enable inputs with two address inputs. Four Double Late Write RAM can be made to look like one larger RAM to the system.

Deselection of the RAM via  $\overline{E1}$  does not deactivate the Echo Clocks.

**Programmable Impedance Output Driver**

The data output and echo clock driver impedance are adjusted by an external resistor, RQ, connected between ZQ pin and Vss, and are equal to RQ/5. For example, 250Ω resistor will give an output impedance of 50Ω. Output driver impedance tolerance is 15% by test(10% by design) and is periodically readjusted to reflect the changes in supply voltage and temperature. Impedance updates occur early in cycles that do not activate the outputs, such as deselect cycles. They may also occur in cycles initiated with  $\overline{G}$  high. In all cases impedance updates are transparent to the user and do not produce access time "push-outs" or other anomalous behavior in the SRAM. Impedance updates occur no more often than every 32 clock cycles. Clock cycles are counted whether the SRAM is selected or not and proceed regardless of the type of cycle being executed. Therefore, the user can be assured that after 33 continuous read cycles have occurred, an impedance update will occur the next time  $\overline{G}$  are high at a rising edge of the K clock. There are no power up requirements for the SRAM. However, to guarantee optimum output driver impedance after power up, the SRAM needs 1024 non-read cycles.

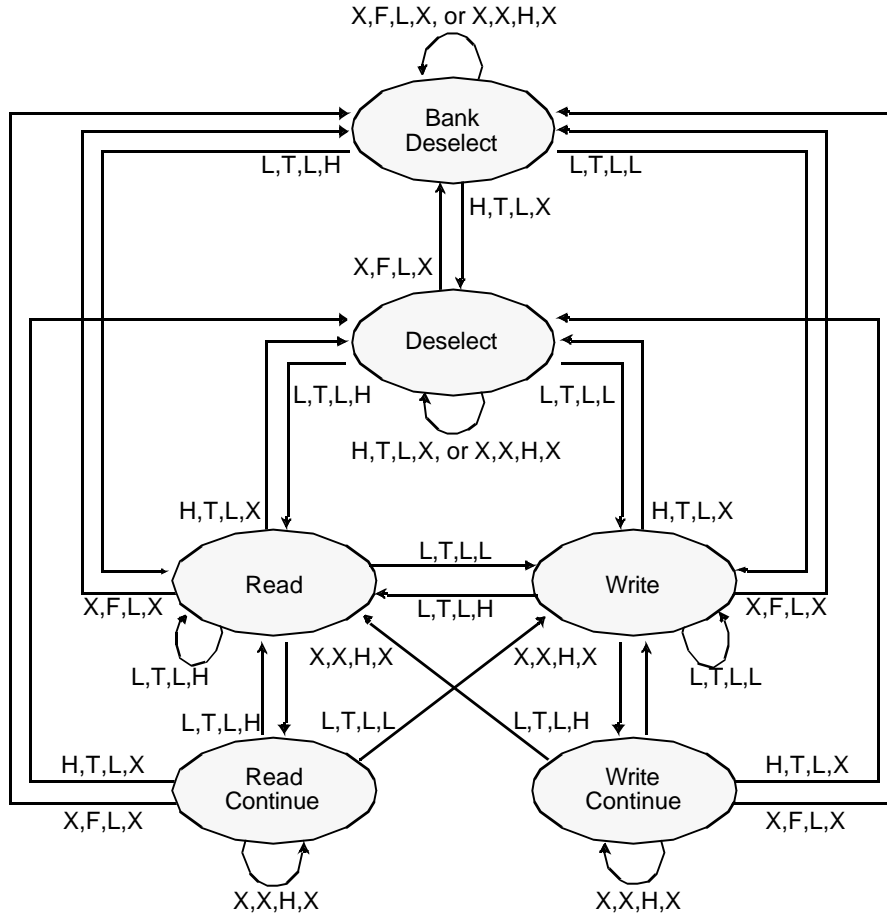
**Example Four Bank Depth Expansion Schematic**



**Bank Enable Truth Table**

	EP2	EP3	E2	E3
Bank 0	VSS	VSS	Active Low	Active Low
Bank 1	VSS	VDD	Active Low	Active High
Bank 2	VDD	VSS	Active High	Active Low
Bank 3	VDD	VDD	Active High	Active High

STATE DIAGRAM FOR Double Late Write RAM



Notes:

1. The notation "X,X,X,X" controlling the state transitions above indicate the states of inputs  $\overline{E1}$ ,  $\overline{E}$ ,  $\overline{ADV}$ , and  $\overline{WE}$  respectively.
2. If (E2=EP2 and E3=EP3) then E="T" else E="F".
3. "H"=input "high"; "L"=input "low"; "X"=input "don't care"; "T"=input "true"; "F"=input "false".



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**TRUTH TABLES**

Previous Cycle	Input Type	$\overline{E1}$ (tn)	E (tn)	ADV (tn)	$\overline{WE}$ (tn)	$\overline{BWx}$ (tn)	Current Operation	Address	DQ/CQ (tn)	DQ/CQ (tn+1)	Notes
N/A	D	H	T	L	X	X	Deselect Cycle	None	*	Hi-Z/CQ	4
Deselect	C	X	X	H	X	X	Deselect Cycle, Continue	Next	Hi-Z/CQ	Hi-Z/CQ	4
N/A	D	X	F	L	X	X	Bank Deselect Cycle	None	*	Hi-Z	4, 5
Bank Deselect	C	X	X	H	X	X	Bank Deselect Cycle, Continue	Next	Hi-Z	Hi-Z	4, 5
N/A	R	L	T	L	H	X	Read Cycle, Begin Burst	External	*	Q/CQ	2
Read	C	X	X	H	X	X	Read Cycle, Continue Burst	Next	Q/CQ	Q/CQ	
N/A	W	L	T	L	L	X	Write Cycle, Begin Burst	External	*	D/CQ	2, 3
N/A	W	L	T	L	L	F	Non-Write Cycle, Begin Burst	External	*	*	2, 3
Write	C	X	X	H	X	T	Write Cycle, Continue Burst	Next	D/CQ	D/CQ	3
Write	C	X	X	H	X	F	Non-Write Cycle, Continue Burst	Next	*	D/CQ	3, 4, 5

**Note:**

1. X=Don't Care, H=High, L=Low.
2. E=T(True) if E2=active and E3=active; E=F(False) if E2=inactive or E3=inactive.
3. "\*" indicates that the DQ input requirement / output state and CQ output state are determined by the previous operation.
4.  $\overline{BWx}$ = F(False) if all Byte Write Enable pins are high.  $\overline{BWx}$ =T(True) if any one Byte Write Enable pin is low.
5. DQs are tri-state in response to Bank Deselect, Deselect, and Write commands.
6. Deassertion of  $\overline{E1}$  does not deactivate the echo clock outputs( CQ1, CQ1 , CQ2, CQ2).

Echo clock outputs are tri-stated in response to Bank Deselect Commands only.

**WRITE TRUTH TABLE(x36)**

$\overline{WE}$	$\overline{BWa}$	$\overline{BWb}$	$\overline{BWc}$	$\overline{BWd}$	OPERATION
H	X	X	X	X	READ
L	L	H	H	H	WRITE BYTE a
L	H	L	H	H	WRITE BYTE b
L	H	H	L	H	WRITE BYTE c
L	H	H	H	L	WRITE BYTE d
L	L	L	L	L	WRITE ALL BYTEs
L	H	H	H	H	WRITE ABORT/NOP

Notes : 1. X means "Don't Care".

2. All inputs in this table must meet setup and hold time around the rising edge of CLK(↑).

**WRITE TRUTH TABLE(x72)**

$\overline{WE}$	$\overline{BWa}$	$\overline{BWb}$	$\overline{BWc}$	$\overline{BWd}$	$\overline{BWe}$	$\overline{BWf}$	$\overline{BWg}$	$\overline{BWh}$	OPERATION
H	X	X	X	X	X	X	X	X	READ
L	L	H	H	H	H	H	H	H	WRITE BYTE a
L	H	L	H	H	H	H	H	H	WRITE BYTE b
L	H	H	L	H	H	H	H	H	WRITE BYTE c
L	H	H	H	L	H	H	H	H	WRITE BYTE d
L	H	H	H	H	L	H	H	H	WRITE BYTE e
L	H	H	H	H	H	L	H	H	WRITE BYTE f
L	H	H	H	H	H	H	L	H	WRITE BYTE g
L	H	H	H	H	H	H	H	L	WRITE BYTE h
L	L	L	L	L	L	L	L	L	WRITE ALL BYTEs
L	H	H	H	H	H	H	H	H	WRITE ABORT/NOP

Notes : 1. X means "Don't Care".

2. All inputs in this table must meet setup and hold time around the rising edge of CLK(↑).

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### ABSOLUTE MAXIMUM RATINGS\*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on V <sub>DD</sub> Supply Relative to V <sub>SS</sub>	V <sub>DD</sub>	-0.5 to 2.9	V
Voltage on V <sub>DDQ</sub> Supply Relative to V <sub>SS</sub>	V <sub>DDQ</sub>	-0.5 to V <sub>DD</sub>	V
Voltage on Any Other Pin Relative to V <sub>SS</sub>	V <sub>IN</sub>	-0.5 to V <sub>DD</sub> +0.3	V
Power Dissipation	P <sub>D</sub>	1.6	W
Storage Temperature	T <sub>STG</sub>	-65 to 150	°C
Operating Temperature	T <sub>OPR</sub>	0 to 70	°C
Storage Temperature Range Under Bias	T <sub>BIAS</sub>	-10 to 85	°C

\*Note : Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

### OPERATING CONDITIONS(0°C ≤ T<sub>A</sub> ≤ 70°C)

PARAMETER	SYMBOL	MIN	Typ.	MAX	UNIT
Supply Voltage	V <sub>DD</sub>	1.7	1.8	1.95	V
	V <sub>DDQ</sub>	1.4	1.5	1.6	V
Ground	V <sub>SS</sub>	0	0	0	V

\*Note : V<sub>DD</sub> and V<sub>DDQ</sub> must be supplied with identical voltage levels.

### DC ELECTRICAL CHARACTERISTICS (V<sub>DD</sub>=1.8V + 150/-100mV, T<sub>A</sub>=0°C to +70°C)

PARAMETER	SYM.	TEST CONDITIONS		MIN	MAX	UNIT	NOTE	
Input Leakage Current	I <sub>IL</sub>	V <sub>DD</sub> =Max ; V <sub>IN</sub> =V <sub>SS</sub> to V <sub>DD</sub>		-2	+2	μA		
Output Leakage Current	I <sub>OL</sub>	Output Disabled,		-2	+2	μA		
Operating Current	I <sub>CC</sub>	V <sub>DD</sub> =Max , I <sub>OUT</sub> =0mA Cycle Time ≥ t <sub>CYC</sub> Min	-35	x72	-	TBD	mA	1,2
				x36	-	TBD		
Standby Current	ISB1	E2 or E3 False, I <sub>OUT</sub> =0mA , f=Max All Inputs ≤ V <sub>IL</sub> or ≥ V <sub>IH</sub>		-	TBD	mA		
	ISB2	E1 ≥ V <sub>IH</sub> , I <sub>OUT</sub> =0mA, f=Max, All Inputs ≤ V <sub>IL</sub> or ≥ V <sub>IH</sub>		-	TBD	mA		
	ISB3	Device deselected, I <sub>OUT</sub> =0mA, f=0, All Inputs=fixed (V <sub>DD</sub> -0.2V or 0.2V)		-	TBD	mA		
Input Low Voltage	V <sub>IL</sub>			-0.3	V <sub>ref</sub> * 0.1	V	3,5,6	
Input High Voltage	V <sub>IH</sub>			V <sub>ref</sub> + 0.1	V <sub>DD</sub> +0.3	V	3,5,7	
Output High Voltage(Programmable Impedance)	V <sub>OH1</sub>			V <sub>DDQ</sub> /2	V <sub>DDQ</sub>	V	8	
Output Low Voltage(Programmable Impedance)	V <sub>OL1</sub>			V <sub>SS</sub>	V <sub>DDQ</sub> /2	V	9	
Output High Voltage(I <sub>OH</sub> =-0.1 mA)	V <sub>OH2</sub>			V <sub>DDQ</sub> -0.2	V <sub>DDQ</sub>	V	10	
Output Low Voltage(I <sub>OL</sub> =0.1 mA)	V <sub>OL2</sub>			V <sub>SS</sub>	0.2	V	10	

- Notes : 1. Reference AC Operating Conditions and Characteristics for input and timing.  
 2. Data states are all zero.  
 3. In Case of I/O Pins, the Max. V<sub>IH</sub>=V<sub>DDQ</sub>+0.3V  
 4. The EP2, EP3 pins must not be changed during operation.  
 5. These are DC test criteria. DC design criteria is V<sub>REF</sub>±50mV. The AC V<sub>IH</sub>/V<sub>L</sub> levels are defined separately for measuring timing parameters.  
 6. V<sub>IL</sub> (Min)DC=-0.3V, V<sub>L</sub> (Min)AC=-1.5V(pulse width ≤ 3ns).  
 7. V<sub>IH</sub> (Max)DC=V<sub>DDQ</sub>+0.3, V<sub>IH</sub> (Max)AC=V<sub>DDQ</sub>+0.85V(pulse width ≤ 3ns).  
 8. |I<sub>OH</sub>|=(V<sub>DDQ</sub>/2)/(RQ/5)±15% @ V<sub>OH</sub>=V<sub>DDQ</sub>/2 for 175Ω ≤ RQ ≤ 350Ω.  
 9. |I<sub>OL</sub>|=(V<sub>DDQ</sub>/2)/(RQ/5)±15% @ V<sub>OL</sub>=V<sub>DDQ</sub>/2 for 175Ω ≤ RQ ≤ 350Ω.  
 10. Minimum Impedance Mode when ZQ pin is connected to V<sub>SS</sub>.

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*Preliminary*

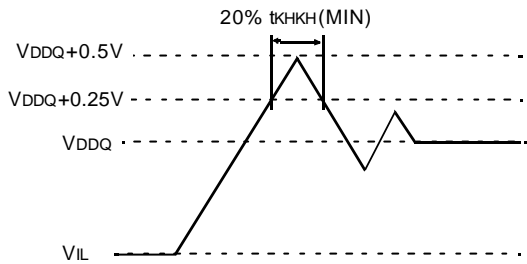
**512Kx36 & 256Kx72 DLW(Double Late Write) RAM**

**CAPACITANCE\*** (TA=25°C, f=1MHz)

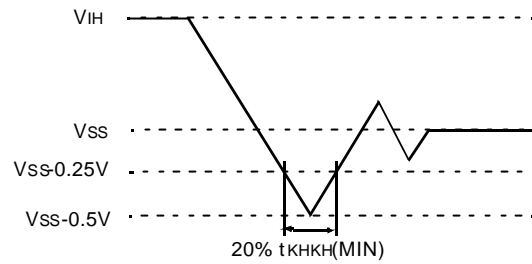
PARAMETER	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Input Capacitance	C <sub>IN</sub>	V <sub>IN</sub> =0V	-	TBD	pF
Output Capacitance	C <sub>OUT</sub>	V <sub>OUT</sub> =0V	-	TBD	pF

\*Note : Sampled not 100% tested.

**Overshoot Timing**



**Undershoot Timing**



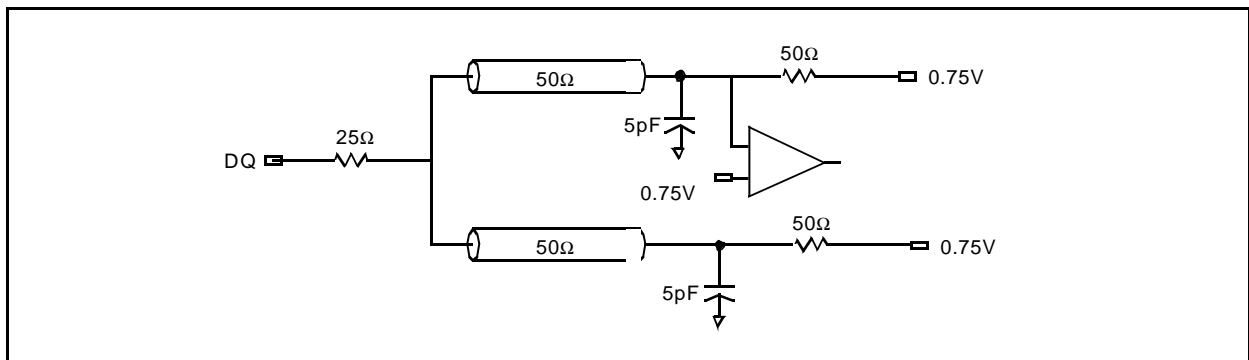
Note: For power-up, V<sub>H</sub> ≤ V<sub>DDQ</sub>+0.3V and V<sub>D</sub> ≤ 1.7V and V<sub>DDQ</sub> ≤ 1.4V t ≤ 200ms

**AC TEST CONDITIONS**

Parameter	Symbol	Value	Unit
Core Power Supply Voltage	V <sub>DD</sub>	1.7~1.9	V
Output Power Supply Voltage	V <sub>DDQ</sub>	1.4~1.6	V
Input High/Low Level	V <sub>IH</sub> /V <sub>IL</sub>	1.25/0.25	V
Input Reference Level	V <sub>REF</sub>	0.75	V
Input Rise/Fall Time	T <sub>R</sub> /T <sub>F</sub>	0.3/0.3	ns
Output Timing Reference Level		V <sub>DDQ</sub> /2	V

Note: Parameters are tested with R<sub>Q</sub>=250Ω

**AC TEST OUTPUT LOAD**



**AC TIMING CHARACTERISTICS** ( $V_{DD}=1.8V + 150/-100mV$ ,  $T_A=0$  to  $70^{\circ}C$ )

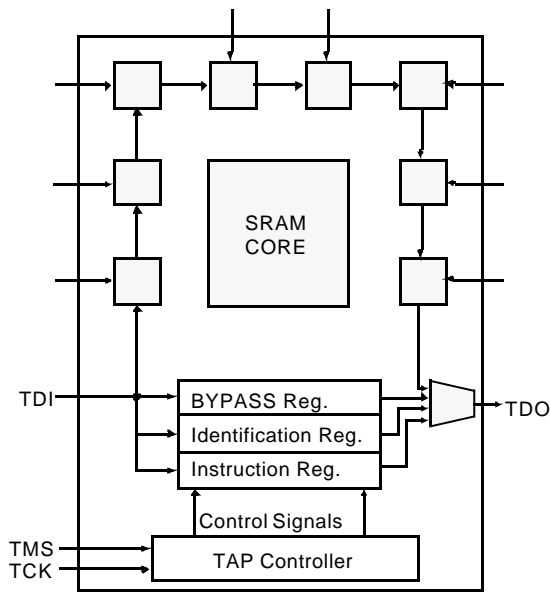
PARAMETER	SYMBOL	-35 SD=VDD		-35 SD=VSS		UNIT
		MIN	MAX	MIN	MAX	
Cycle Time	tKHKH	2.85	-	2.85	-	ns
Clock High to Output Valid	tKHQV	-	1.7	-	2.6	ns
Clock High to Output High-Z	tKHQZ	0.5	1.7	1.4	2.6	ns
Output Hold from Clock High	tKHQX	0.5	-	1.4	-	ns
Clock High to Output Low-Z	tKHQX1	0.5	-	1.4	-	ns
Clock High to CQ High	tKHCH	0.5	1.7	1.4	2.6	ns
Clock Low to CQ Low	tKLCL	0.5	1.7	1.4	2.6	ns
Output Hold from CQ High	tCHQX	-0.4	-	-0.4	-	ns
CQ High to Output Low-Z	tCHQX1	-0.4	-	-0.4	-	ns
CQ High to Output Valid	tCHQV	-	0.4	-	0.4	ns
Clock High to CQ Low-Z	tKHCX1	0.5	-	1.4	-	ns
Clock High to CQ High-Z	tKHCZ	0.5	1.5	1.4	2.4	ns
Clock High Pulse Width	tKHKL	1.2	-	1.2	-	ns
Clock Low Pulse Width	tKLKH	1.2	-	1.2	-	ns
Address Setup to Clock High	tAVKH	0.6	-	0.6	-	ns
Chip Enable Setup to Clock High	tEVKH	0.6	-	0.6	-	ns
Write Setup to Clock High( $\overline{WE}$ , $\overline{BWx}$ )	tWVKH	0.6	-	0.6	-	ns
Data Setup to Clock High	tDVKH	0.6	-	0.6	-	ns
Address Advance Setup to Clock High	tadvVKH	0.6	-	0.6	-	ns
Address Hold from Clock High	tKHAX	0.4	-	0.4	-	ns
Chip Enable Hold from Clock High	tKHEX	0.4	-	0.4	-	ns
Write Hold from Clock High( $\overline{WE}$ , $\overline{BWx}$ )	tKHwx	0.4	-	0.4	-	ns
Data Hold from Clock High	tKHDX	0.4	-	0.4	-	ns
Address Advance Hold from Clock High	tKHadvX	0.4	-	0.4	-	ns

- Notes :**
1. All address inputs must meet the specified setup and hold times for all rising clock(CLK) edges when ADV is sampled low and  $\overline{E1}$  is sampled low. All other synchronous inputs must meet the specified setup and hold times whenever this device is chip selected.
  2. Chip selects must be valid at each rising edge of CLK(when ADV is Low) to remain enabled.
  3. A write cycle is defined by  $\overline{WE}$  low having been registered into the device at ADV Low, A Read cycle is defined by  $\overline{WE}$  High with ADV Low, Both cases must meet setup and hold times.
  4. To avoid bus contention, At a given voltage and temperature tKHQX1 is more than tKHQZ.  
 The specs as shown do not imply bus contention because tKHQX1 is a Min. parameter that is worst case at totally different test conditions (0°C,1.95V) than tKHQZ, which is a Max. parameter(worst case at 70°C,1.7V)  
 It is not possible for two SRAMs on the same board to be at such different voltage and temperature.

**IEEE 1149.1 TEST ACCESS PORT AND BOUNDARY SCAN-JTAG**

This part contains an IEEE standard 1149.1 Compatible Test Access Port(TAP). The package pads are monitored by the Serial Scan circuitry when in test mode. This is to support connectivity testing during manufacturing and system diagnostics. Internal data is not driven out of the SRAM under JTAG control. In conformance with IEEE 1149.1, the SRAM contains a TAP controller, Instruction Register, Bypass Register and ID register. The TAP controller has a standard 16-state machine that resets internally upon power-up, therefore, TRST signal is not required. It is possible to use this device without utilizing the TAP. To disable the TAP controller without interfacing with normal operation of the SRAM, TCK must be tied to V<sub>ss</sub> to preclude mid level input. TMS and TDI are designed so an undriven input will produce a response identical to the application of a logic 1, and may be left unconnected. But they may also be tied to V<sub>DD</sub> through a resistor. TDO should be left unconnected.

**JTAG Block Diagram**



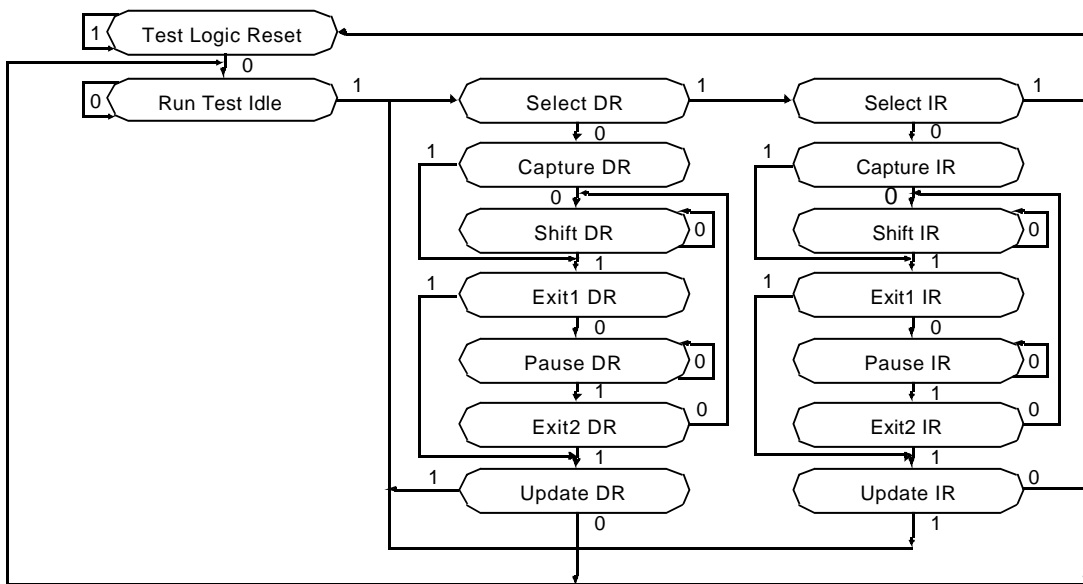
**JTAG Instruction Coding**

IR2	IR1	IR0	Instruction	TDO Output	Notes
0	0	0	EXTEST	Boundary Scan Register	1
0	0	1	IDCODE	Identification Register	3
0	1	0	SAMPLE-Z	Boundary Scan Register	2
0	1	1	BYPASS	Bypass Register	4
1	0	0	SAMPLE	Boundary Scan Register	5
1	0	1	RESERVED	Do Not Use	6
1	1	0	BYPASS	Bypass Register	4
1	1	1	BYPASS	Bypass Register	4

**NOTE :**

1. Places DQs in Hi-Z in order to sample all input data regardless of other SRAM inputs. This instruction is not IEEE 1149.1 compliant.
2. Places DQs in Hi-Z in order to sample all input data regardless of other SRAM inputs.
3. TDI is sampled as an input to the first ID register to allow for the serial shift of the external TDI data.
4. Bypass register is initiated to V<sub>ss</sub> when BYPASS instruction is invoked. The Bypass Register also holds serially loaded TDI when exiting the Shift DR states.
5. SAMPLE instruction dose not places DQs in Hi-Z.
6. This instruction is reserved for future use.

**TAP Controller State Diagram**



**K7Z167288B**  
**K7Z163688B**

**512Kx36 & 256Kx72 DLW(Double Late Write) RAM**

**SCAN REGISTER DEFINITION**

Part	Instruction Register	Bypass Register	ID Register	Boundary Scan
512Kx36	3 bits	1 bits	32 bits	121 bits
256Kx72	3 bits	1 bits	32 bits	121 bits

**ID REGISTER DEFINITION**

Part	Revision Number (31:28)	Part Configuration (27:18)	Vendor Definition (17:12)	Samsung JEDEC Code (11: 1)	Start Bit(0)
512Kx36	0000	00111 00100	XXXXXX	00001001110	1
256Kx72	0000	00110 00101	XXXXXX	00001001110	1

**BOUNDARY SCAN EXIT ORDER**

Order	Pin ID	Order	Pin ID
1	6W	36	11H
2	6V	37	10H
3	6U	38	10G
4	7V	39	11G
5	7U	40	11F
6	7W	41	10F
7	8U	42	10E
8	8V	43	11E
9	9V	44	11D
10	10W	45	10D
11	11W	46	10C
12	11V	47	11C
13	10V	48	11B
14	10U	49	10B
15	11U	50	10A
16	11T	51	11A
17	10T	52	9C
18	11R	53	9B
19	10R	54	9A
20	10P	55	8C
21	11P	56	8B
22	11N	57	8A
23	10N	58	7B
24	10M	59	7A
25	11M	60	6H
26	11L	61	6G
27	10L	62	6D
28	11K	63	6C
29	6M	64	6B
30	6L	65	6A
31	6J	66	5C
32	6F	67	5A
33	10K	68	4C
34	10J	69	4B
35	11J	70	5B

Order	Pin ID	Order	Pin ID
71	4A	106	2R
72	3C	107	1R
73	3B	108	1T
74	3A	109	2T
75	2A	110	2U
76	1A	111	1U
77	1B	112	1V
78	2B	113	2V
79	2C	114	2W
80	1C	115	1W
81	1D	116	3V
82	2D	117	4V
83	1E	118	4U
84	2E	119	5U
85	2F	120	5V
86	1F	121	5W
87	1G		
88	2G		
89	2H		
90	1H		
91	1J		
92	2J		
93	1K		
94	6N		
95	3K		
96	4K		
97	2K		
98	2L		
99	1L		
100	1M		
101	2M		
102	2N		
103	1N		
104	1P		
105	2P		

NOTE, NC,MCL and MCH ; Don't Care

**JTAG DC OPERATING CONDITIONS**

Parameter	Symbol	Min	Typ	Max	Unit	Note
Power Supply Voltage	VDD	1.7	1.8	1.95	V	
Input High Level	V <sub>IH</sub>	1.3	-	V <sub>DD</sub> +0.3	V	1
Input Low Level	V <sub>IL</sub>	-0.3	-	0.5	V	
Output High Voltage(I <sub>OH</sub> =-2mA)	V <sub>OH</sub>	1.5	-	V <sub>DD</sub>	V	
Output Low Voltage(I <sub>OL</sub> =2mA)	V <sub>OL</sub>	V <sub>SS</sub>	-	0.45	V	

\*Note : 1. In Case of I/O Pins, the Max. V<sub>IH</sub>=V<sub>DDQ</sub>+0.3V

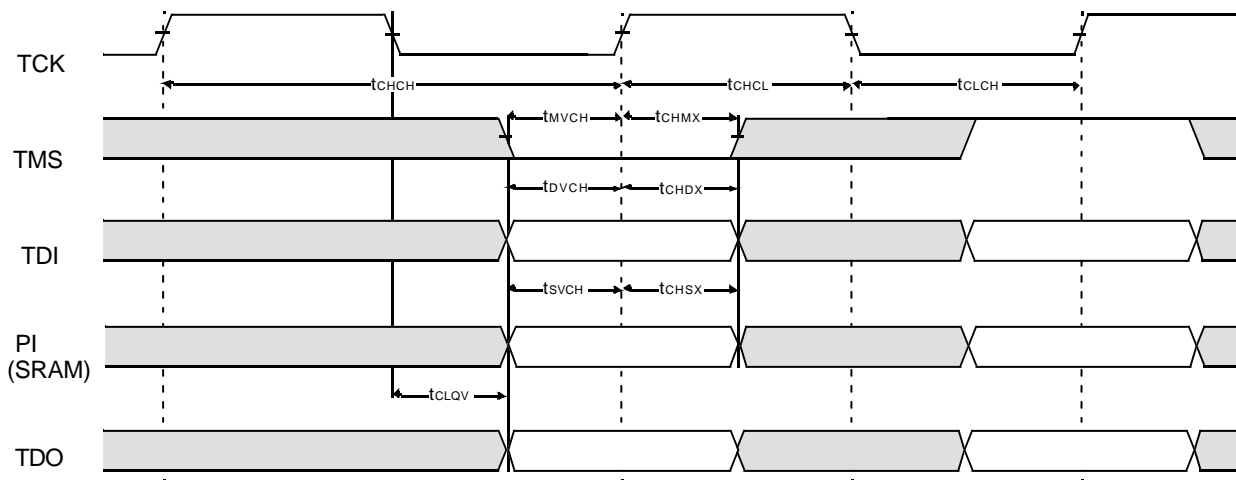
**JTAG AC TEST CONDITIONS**

Parameter	Symbol	Min	Unit	Note
Input High/Low Level	V <sub>IH</sub> /V <sub>IL</sub>	1.3/0.5	V	
Input Rise/Fall Time	TR/TF	1.0/1.0	ns	
Input and Output Timing Reference Level		0.9	V	

**JTAG AC Characteristics**

Parameter	Symbol	Min	Max	Unit	Note
TCK Cycle Time	t <sub>CHCH</sub>	20	-	ns	
TCK High Pulse Width	t <sub>CHCL</sub>	10	-	ns	
TCK Low Pulse Width	t <sub>CLCH</sub>	10	-	ns	
TMS Input Setup Time	t <sub>MVCH</sub>	5	-	ns	
TMS Input Hold Time	t <sub>CHMX</sub>	5	-	ns	
TDI Input Setup Time	t <sub>DVCH</sub>	5	-	ns	
TDI Input Hold Time	t <sub>CHDX</sub>	5	-	ns	
SRAM Input Setup Time	t <sub>SVCH</sub>	5	-	ns	
SRAM Input Hold Time	t <sub>CHSX</sub>	5	-	ns	
Clock Low to Output Valid	t <sub>CLQV</sub>	0	10	ns	

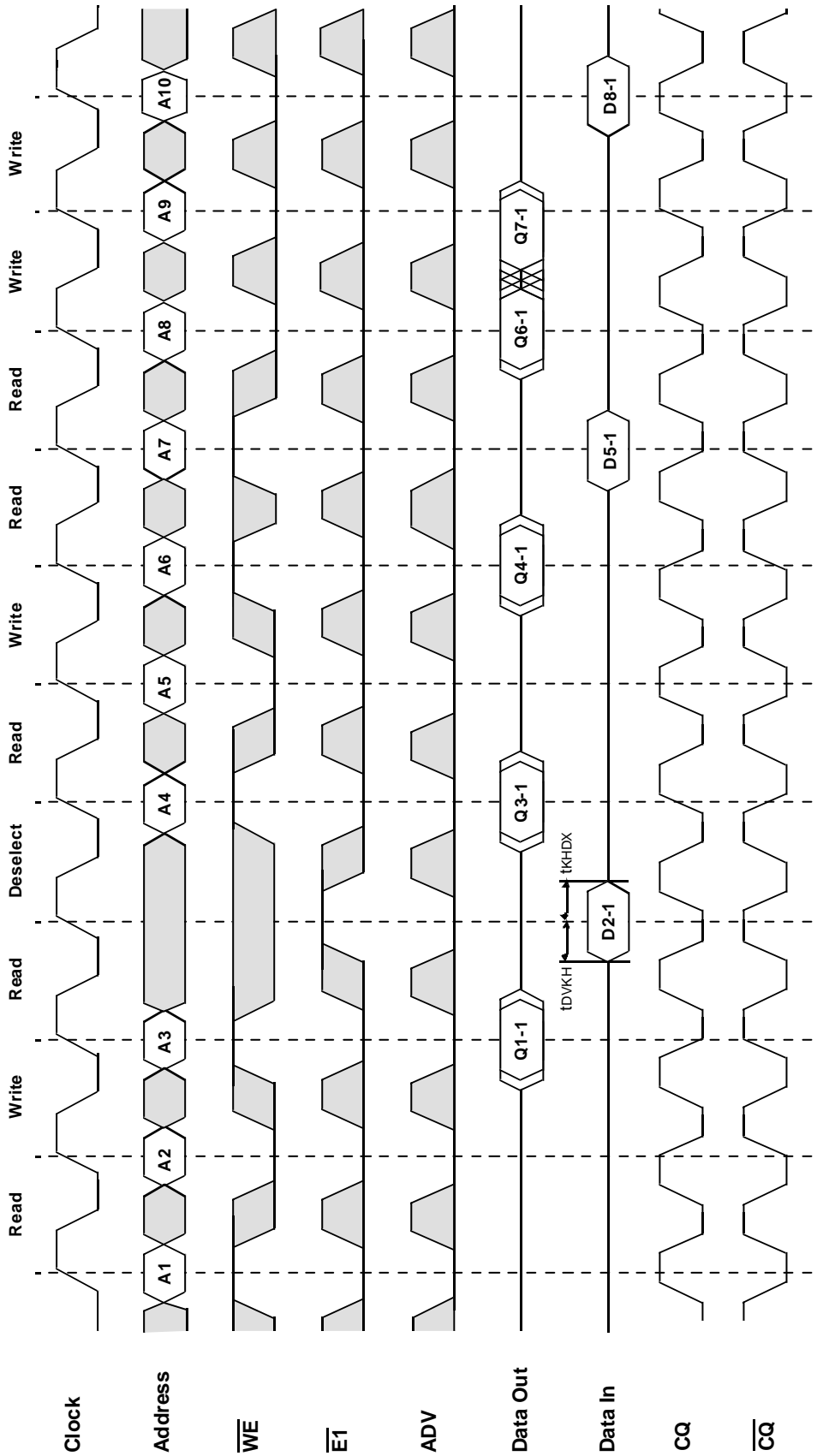
**JTAG TIMING DIAGRAM**





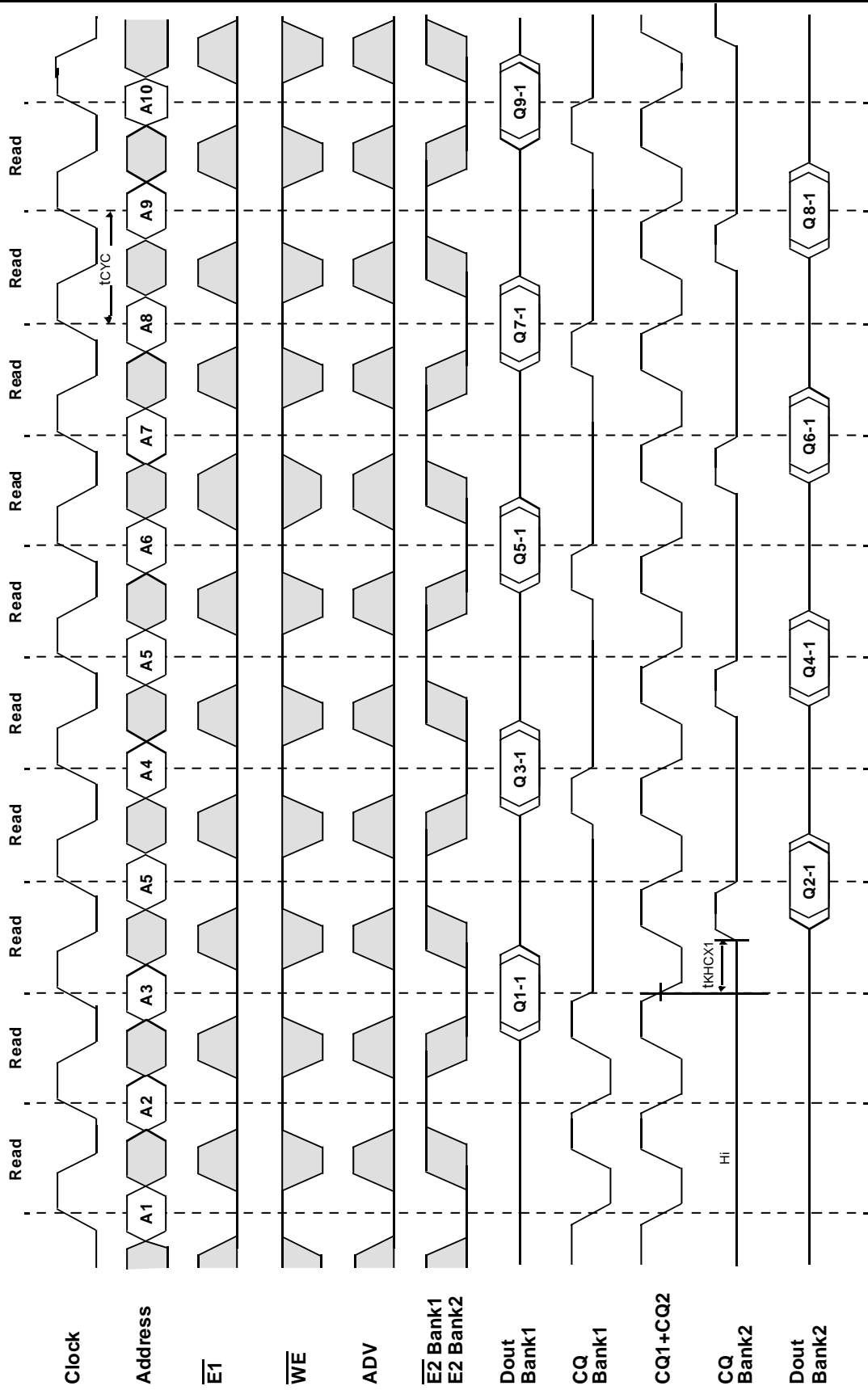


TIMING WAVEFORM OF SINGLE READ/WRITE



□ Don't Care  
▣ Undefined

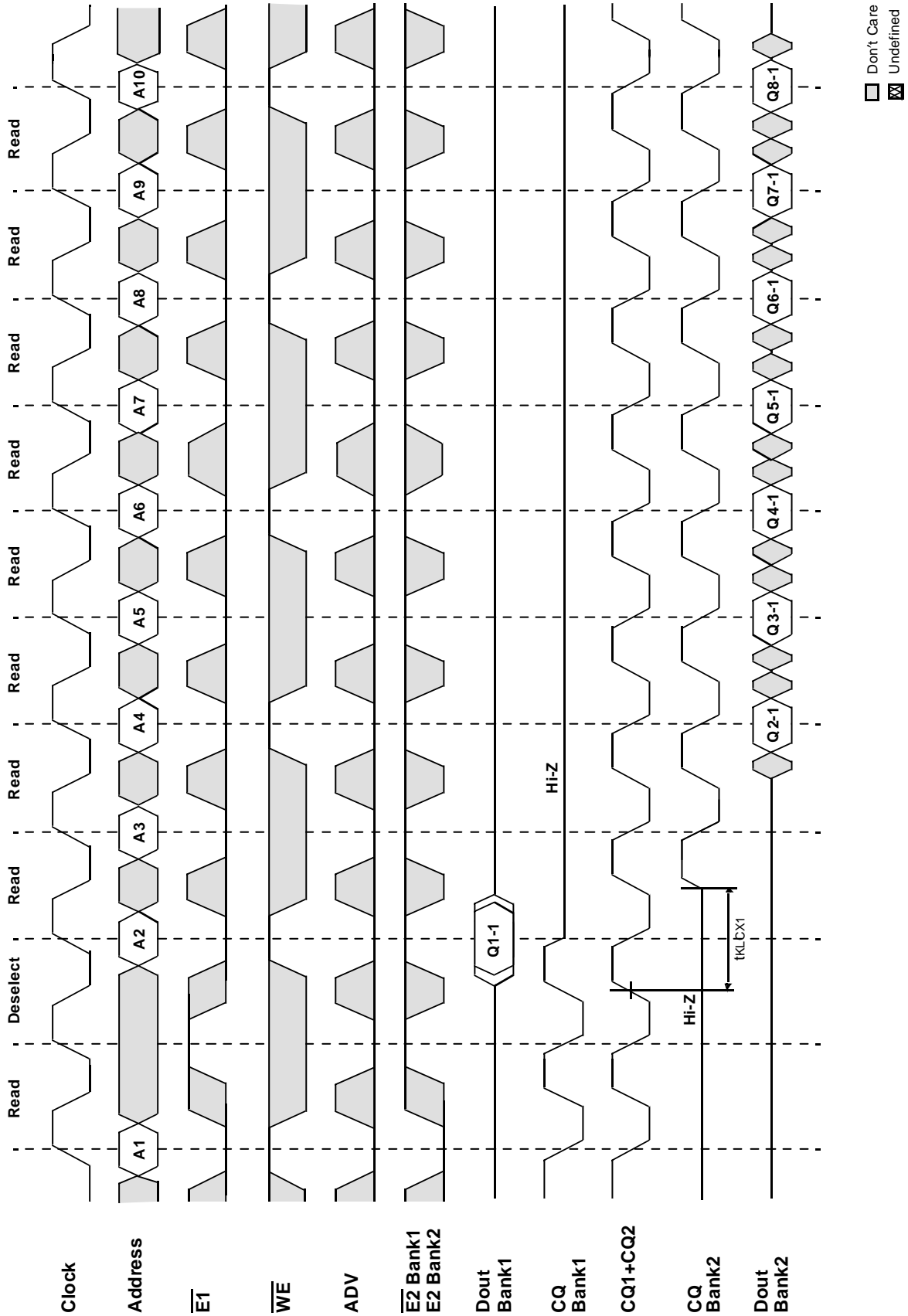
ECHO CLOCK CONTROL IN TWO BANKS



□ Don't Care  
▣ Undefined

NOTE:  $\overline{E1}$  does not deselect the Echo Clock Outputs. Echo Clock Outputs are deselected by E2 or E3 being sampled false.

BANK SWITCH WITH  $\overline{E1}$  DESELECT

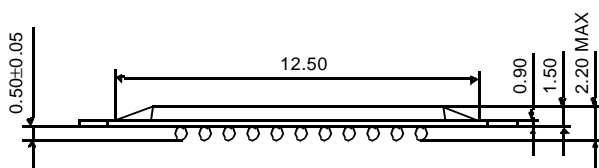
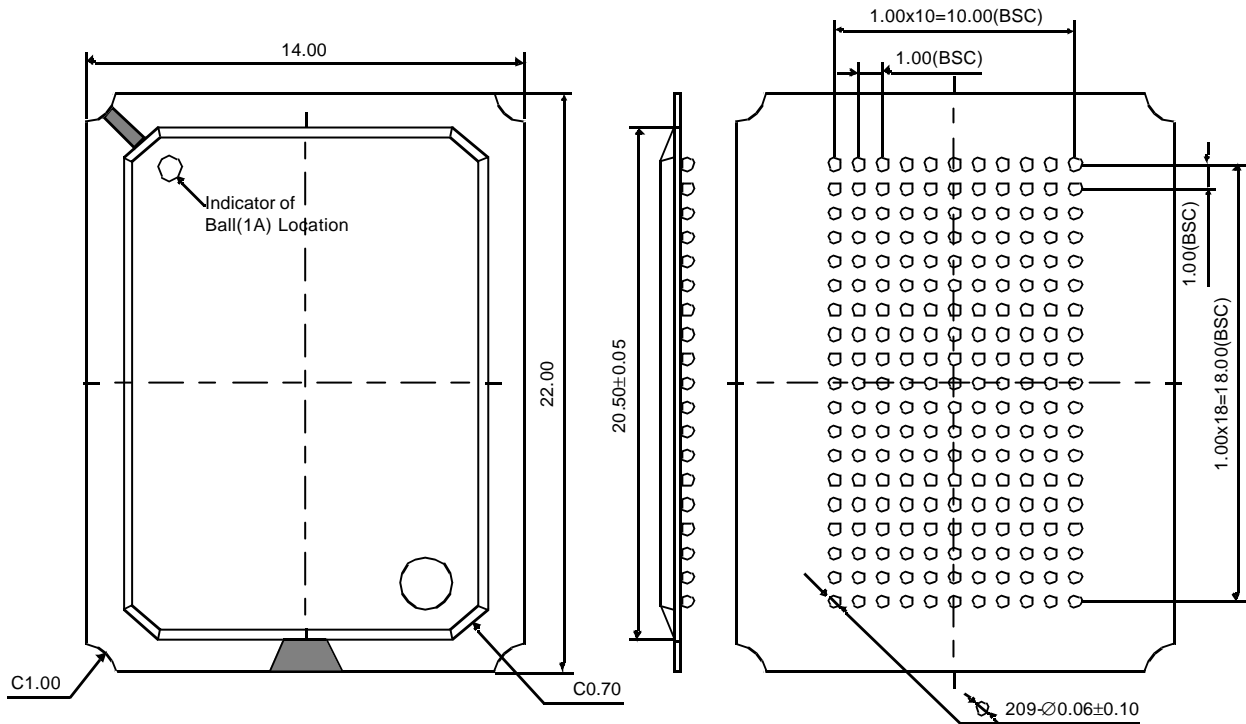


K7Z167288B  
K7Z163688B

512Kx36 & 256Kx72 DLW(Double Late Write) RAM

209 Bump BGA PACKAGE DIMENSIONS

14mm x 22mm Body, 1.0mm Bump Pitch, 11x19 Bump Array



NOTE :

1. All Dimensions are in Millimeters.
2. Solder Ball to PCB Offset: 0.10 MAX.
3. PCB to Cavity Offset: 0.10 MAX.